

ALTERNATIVE TO PTO/SB/08A/B
(Based on PTO 08-08 version)

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete if Known		
			Application Number	10/537,804	
			Filing Date	June 7, 2005	
			First Named Inventor	Robert DWILINSKI	
			Art Unit	1792	
			Examiner Name	F. C. Hiteshew	
			Attorney Docket Number	204552035400	
Sheet	1	of	3		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1.	US-6,177,292-B1	01-23-2001	Hong et al.	
	2.	US-6,248,607-B1	06-19-2001	Tsutsui	
	3.	US-6,355,497-B1	03-12-2002	Romano et al.	
	4.	US-6,475,277-B1	11-05-2002	Hirota et al.	
	5.	US-2002/0192507-A1	12-19-2002	Dwilinski et al.	
	6.	US-6,627,552-B1	09-30-2003	Nishio et al.	
	7.	US-6,639,925-B2	10-28-2003	Niwa et al.	
	8.	US-6,653,663-B2	11-25-2003	Ishida	
	9.	US-6,686,608-B1	02-03-2004	Takahira	
	10.	US-6,693,935-B2	02-17-2004	Tojo et al.	
	11.	US-2004/0089221-A1	05-13-2004	Dwilinski et al.	
	12.	US-6,749,819-B2	06-15-2004	Otsuka et al.	
	13.	US-2004/0238810-A1	12-02-2004	Dwilinski et al.	
	14.	US-2004/0251471-A1	12-16-2004	Dwilinski et al.	
	15.	US-2004/0261692-A1	12-30-2004	Dwilinski et al.	
	16.	US-2005/0087124-A1	04-28-2005	Dwilinski et al.	
	17.	US-2005/0249255-A1	11-10-2005	Dwilinski et al.	
	18.	US-2006/0054075-A1	03-16-2006	Dwilinski et al.	
	19.	US-2006/0054076-A1	03-16-2006	Dwilinski et al.	
	20.	US-2006/0057749-A1	03-16-2006	Dwilinski et al.	
	21.	US-2006/0124051-A1	06-15-2006	Yoshioka et al.	
	22.	US-2006/0138431-A1	06-29-2006	Dwilinski et al.	
	23.	US-7,252,712-B1	08-07-2007	Dwilinski et al.	
	24.	US-7,314,517-B2	01-01-2008	Dwilinski et al.	
	25.	US-7,315,599-B2	01-01-2008	Morris	
	26.	US-7,335,262-B2	02-26-2008	Dwilinski et al.	
	27.	US-2008/0050855-A1	02-28-2008	Dwilinski et al.	
	28.	US-7,364,619-B2	04-29-2008	Dwilinski et al.	
	29.	US-2008/0108162-A1	05-08-2008	Dwilinski et al.	
	30.	US-7,374,615-B2	05-20-2008	Dwilinski et al.	
	31.	US-7,387,877-B2	06-17-2008	Dwilinski et al.	
	32.	US-2008/0156254-A1	07-03-2008	Dwilinski et al.	
	33.	US-7,420,261-B2	09-02-2008	Dwilinski et al.	
	34.	US-7,422,633-B2	09-09-2008	Dwilinski et al.	

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
		Country Code ² -Number-Kind Code ² (if known)			
	35.	JP-51-41686	04-08-1976	Matsushita Electric Industrial Co., Ltd.	Translation of abstract
	36.	WO-94/28204	12-08-1994	Technalium Research, Inc.	
	37.	WO-97/13891	04-17-1997	Centrum Badan Wysokocisnieniowych	
	38.	JP-9-508093	08-19-1997		Corresponds to WO-94/28204 listed above

ALTERNATIVE TO PTO/SB/08A/B
(Based on PTO 08-08 version)

Substitute for form 1449/PTO		Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Application Number	10/537,804		
		Filing Date	June 7, 2005		
		First Named Inventor	Robert DWILINSKI		
		Art Unit	1792		
		Examiner Name	F. C. Hiteshew		
Sheet	2	of	3	Attorney Docket Number	204552035400

	39.	JP-2000-327495	11-28-2000	Japan Science and Technology Corp.		✓
	40.	JP-2001-077038	03-23-2001	Sumitomo Electric Industries	Translation of abstract and corresponds to US-6,475,277 listed above	
	41.	EP-1 164 210-A2	12-19-2001	Sharp Kabushiki Kaisha		
	42.	JP-2002-026442	01-25-2002	Sony Corp.	Translation of abstract	
	43.	PL-347918	12-16-2002	Ammono SP.Zo.o; Nichia Corporation		✓
	44.	WO-02/101124-A1	12-19-2002	Nichia Corporation	Translation of abstract	
	45.	PL-350375	05-05-2003	Ammono SP.Zo.o; Nichia Corporation		✓
	46.	EP-1 405 936-A1	04-07-2004	Ammono SP. Zo.o		
	47.	WO-2004/090202-A1	10-21-2004	Mitsubishi Chemical Corporation; Tokyo Denpa Co., Ltd.	Translation of abstract	
	48.	EP-1 616 981-A1	01-18-2006	Tokyo Denpa Co., Ltd.; Mitsubishi Chemical Corporation		
	49.	CN-1260409	06-21-2006	Ammono SP. ZO.O	Translation of abstract and corresponds to WO-02/101124 listed above	

*EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinda Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T ²
	50.	Supplementary European Search Report, dated September 23, 2008, European Patent Application No.02788783.5; 3 pages				
	51.	Chinese Office Action, dated July 18, 2008, directed to Chinese Patent Application No. 200580040008.X; 25 pages				✓
	52.	Chinese Office Action, dated December 28, 2007, directed to Chinese Patent Application No. 02802023.5; 8 pages				✓
	53.	Japanese Notification, mailed March 14, 2006, directed to Japanese Patent Application No. 2003-50367; 3 pages				✓
	54.	Japanese Notification of Reason(s) for Refusal, mailed December 16, 2008, directed to Japanese Patent Application No. 2004-505416; 7 pages				✓
	55.	Japanese Notification of Reason(s) for Refusal, mailed January 6, 2009, directed to Japanese Patent Application No. 2004-506101; 7 pages				✓

ALTERNATIVE TO PTO/SB/08A/B
(Based on PTO 08-08 version)

Substitute for form 1449/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Application Number	10/537,804
		Filing Date	June 7, 2005
		First Named Inventor	Robert DWILINSKI
		Art Unit	1792
		Examiner Name	F. C. Hiteshew
		Attorney Docket Number	204552035400
Sheet	3	of	3

56.	International Search Report, mailed May 7, 2004, directed to International Patent Application No. PCT/JP03/15906; 3 pages	
57.	International Search Report, mailed September 29, 2005, directed to International Patent Application No. PCT/JP2005/011091; 3 pages	
58.	International Search Report, mailed April 21, 2006, directed to International Patent Application No. PCT/JP2005/022396; 3 pages	
59.	U.S. Office Action, mailed October 16, 2007, directed to U.S. Patent Application No. 10/538,654; 10 pages	
60.	U.S. Office Action, mailed April 2, 2007, directed to U.S. Patent Application No. 10/538,407; 13 pages	
61.	Song, Y. et al. (2003). "Bulk GaN Single Crystals: Growth Conditions by Flux Method." <i>Journal of Crystal Growth</i> . 247:275-278	
62.	Beaumont, B. et al. (2001). "Epitaxial Lateral Overgrowth of GaN." <i>Phys. Stat. Sol.(b)</i> . 227(1); 1-43	
63.	Liu, L. et al. (2002). "Substrates for Gallium Nitride Epitaxy." <i>Reports: A Review Journal, Materials Science and Engineering</i> . 37:61-127	
64.	Yano, M. et al. (2000). "Growth of Nitride Crystals, BN, AlN and GaN by Using a Na Flux" <i>Diamond and Related Materials</i> . 9:512-515	
65.	Yamane, H. et al. (July 1, 1998). "Na Flux Growth of GaN Single Crystals" <i>Journal of the Japanese Association for Crystal Growth</i> . 25(4):14-18	
66.	Yamane, H. et al. (1998). "Morphology and Characterization of GaN Single Crystals Grown in a Na Flux." <i>Journal of Crystal Growth</i> . 186:8-12	
67.	Purdy, A. "Ammonothermal Synthesis of Cubic Gallium Nitride." <i>American Chemical Society. Chem. Mater.</i> 11(7):1648-1651	
68.	Sangwal, K. (1994). "Growth Apparatus." Chapter 10.3 <i>In Elementary Crystal Growth</i> . Lublin:331	
69.	Ikornikova, N. I. O. (1975). "Hydrothermal Synthesis of Crystals in Chloride Systems," <i>Izd. Nauka, ed. Moscow</i> : 124-125; 132-133	✓
70.	Lan, Y. C. et al., (April 14, 2000). "Syntheses and Structure of Nanocrystalline Gallium Nitride Obtained from Ammonothermal Method Using Lithium Metal as Mineralizer," <i>Materials Research Bulletin</i> 35:2325-2330.	
71.	Polish Patent Office Notification and Search Report, dated January 15, 2007, directed to Polish Patent Application No. P-347918/DP. 8 pages	✓
72.	Penkala, T., (1972). "Zarys Krystalografii (Basics of Crystallography)". PWN, Warszawa: 349	✓

Examiner Signature	/Felisa Hiteshew/	Date Considered	06/05/2009
--------------------	-------------------	-----------------	------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.